

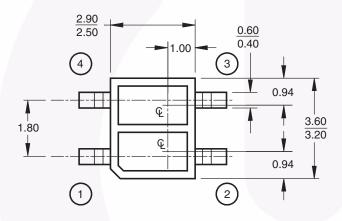
January 2008

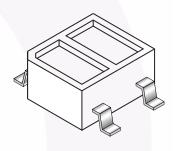
# QRE1113GR SMT Reflective Object Sensor

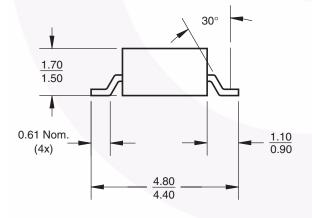
### **Features**

- Phototransistor output
- Tape and reel packaging
- No contact surface sensing
- Miniature package
- Lead form style: Gull Wing

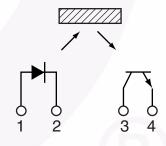
# **Package Dimensions**







### **Schematic**



- PIN 1 ANODE
- PIN 3 COLLECTOR
- PIN 2 CATHODE
- PIN 4 EMITTER

### Notes:

- 1. Dimensions for all drawings are in millimeters.
- 2. Tolerance of ±0.15mm on all non-nominal dimensions

### **Absolute Maximum Ratings** (T<sub>A</sub> = 25°C unless otherwise specified)

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameter	Rating	Units	
T <sub>OPR</sub>	Operating Temperature	-40 to +85	-40 to +85 °C	
T <sub>STG</sub>	Storage Temperature	-40 to +90		
T <sub>SOL-I</sub>	Soldering Temperature (Iron) <sup>(2,3,4)</sup>	240 for 5 sec °C		
T <sub>SOL-F</sub>	Soldering Temperature (Flow) <sup>(2,3)</sup>	Flow) <sup>(2,3)</sup> 260 for 10 sec		
EMITTER				
I <sub>F</sub>	Continuous Forward Current	50	mA	
V <sub>R</sub>	Reverse Voltage	5	5 V	
I <sub>FP</sub>	Peak Forward Current <sup>(5)</sup>	1	Α	
P <sub>D</sub>	Power Dissipation <sup>(1)</sup>	75	mW	
SENSOR				
V <sub>CEO</sub>	Collector-Emitter Voltage	30	V	
V <sub>ECO</sub>	Emitter-Collector Voltage	5	V	
I <sub>C</sub>	Collector Current	20	mA	
$P_{D}$	Power Dissipation <sup>(1)</sup>	50	mW	

### **Electrical/Optical Characteristics** (T<sub>A</sub> = 25°C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
INPUT DIOI	DE				•	
V <sub>F</sub>	Forward Voltage	I <sub>F</sub> = 20mA		1.2	1.6	V
I <sub>R</sub>	Reverse Leakage Current	$V_R = 5V$			10	μΑ
$\lambda_{PE}$	Peak Emission Wavelength	I <sub>F</sub> = 20mA		940		nm
OUTPUT TRANSISTOR						
I <sub>D</sub>	Collector-Emitter Dark Current	$V_{CE} = 20V$ , $I_F = 0mA$			100	nA
COUPLED						
I <sub>C(ON)</sub>	On-State Collector Current	$I_F = 20 \text{mA}, V_{CE} = 5V^{(6)}$	0.10	0.40		mA
V <sub>CE (SAT)</sub>	Saturation Voltage				0.3	V
t <sub>r</sub>	Rise Time	$V_{CC} = 5V$ , $I_{C(ON)} = 100\mu A$ , $R_1 = 1k\Omega$		20		μs
t <sub>f</sub>	Fall Time	$R_L = 1k\Omega$		20		

#### Notes:

- 1. Derate power dissipation linearly 1.00mW/°C above 25°C.
- 2. RMA flux is recommended.
- 3. Methanol or isopropyl alcohols are recommended as cleaning agents.
- 4. Soldering iron 1/16" (1.6mm) from housing.
- 5. Pulse conditions:  $tp = 100\mu s$ ; T = 10ms.
- 6. Measured using an aluminum alloy mirror at d = 1mm.

# **Typical Performance Curves**

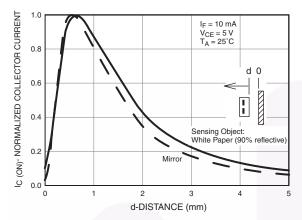


Fig. 1 Normalized Collector Current vs. Distance between device and reflector

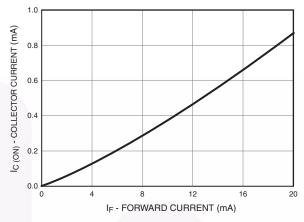


Fig. 2 Collector Current vs. Forward Current

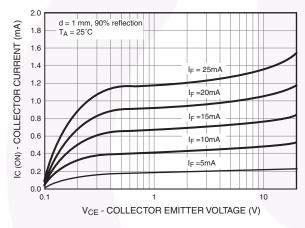


Fig. 3 Collector Current vs. Collector to Emitter Voltage

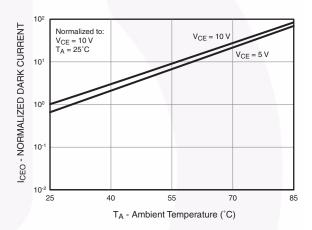


Fig. 4 Collector Emitter Dark Current (Normalized) vs. Ambient Temperature

# **Typical Performance Curves** (Continued)

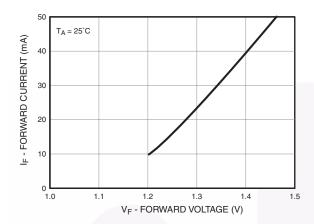


Fig. 6 Forward Current vs. Forward Voltage

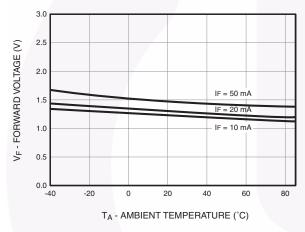


Fig. 8 Forward Voltage vs. Ambient Temperature

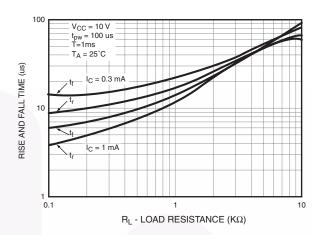


Fig. 7 Rise and Fall Time vs. Load Resistance

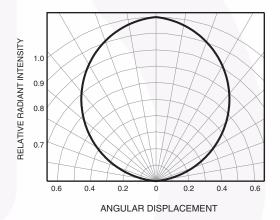
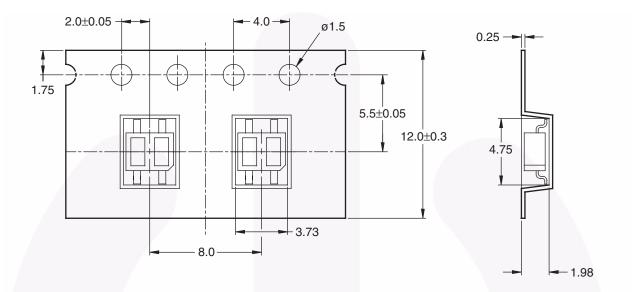


Fig. 8 Radiation Diagram

# **Taping Dimensions**

### Progressive Direction



General tolerance ±0.1 Dimensions in mm





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